

# **$\sigma$ -Hole Interactions: An Umbrella Encompassing Group IV, Pnicogens, Chalcogens and Halogens**

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A  $\sigma$ -hole bond is a noncovalent interaction between a covalently-bonded atom of Groups IV–VII and a negative site, e.g. a lone pair of a Lewis base, a  $\pi$ -region of an unsaturated system or an anion [1]. It involves a region of positive electrostatic potential, labeled a  $\sigma$ -hole, on the extension of one of the covalent bonds to the Group IV – VII atom. The  $\sigma$ -hole is due to the anisotropy of the atom's charge distribution that is the result of covalent  $\sigma$  bond formation. Halogen bonding [2] is a subset of  $\sigma$ -hole interactions, and is increasingly being recognized for numerous innovative applications in crystal engineering [3] and pharmaceutical [4] applications. The features and properties of  $\sigma$ -hole bonds can be fully explained in terms of electrostatics and polarization plus dispersion [1,5,6]. The strengths of the interactions generally correlate well with the magnitudes of the positive and negative electrostatic potentials of the  $\sigma$ -hole and the negative site. In certain instances, however, polarizabilities must be taken into account explicitly, as the polarization of the negative site reaches a level that can be viewed as a degree of dative sharing of electronic charge (coordinate covalence) [7]. This presentation will provide an overview of  $\sigma$ -hole interactions.

## **References**

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